

4.34 Determine the equilibrium electron and hole concentrations in silicon for the following conditions:

(a) $T = 300 \text{ K}$, $N_d = 10^{15} \text{ cm}^{-3}$, $N_a = 4 \times 10^{15} \text{ cm}^{-3}$

(b) $T = 300 \text{ K}$, $N_d = 3 \times 10^{16} \text{ cm}^{-3}$, $N_a = 0$

Table B.4, $n_i = 1.5 \times 10^{10} \text{ #/cm}^3$

a) For $N_a > N_d$ and assuming complete ionization, we can use (4.62)

$$p_0 = \frac{N_a - N_d}{2} + \sqrt{\left(\frac{N_a - N_d}{2}\right)^2 + n_i^2} = \frac{3 \times 10^{15}}{2} + \sqrt{\left(\frac{3 \times 10^{15}}{2}\right)^2 + (1.5 \times 10^{10})^2}$$

$$\underline{p_0 = 3 \times 10^{15} \text{ #/cm}^3}$$

$$(4.43) \quad n_0 p_0 = n_i^2 \Rightarrow n_0 = \frac{n_i^2}{p_0}$$

$$n_0 = \frac{(1.5 \times 10^{10})^2}{3 \times 10^{15}} \Rightarrow \underline{n_0 = 7.5 \times 10^4 \text{ #/cm}^3}$$

b) Assuming complete ionization and noting $N_d > N_a$, we can use (4.60)

$$n_0 = \frac{N_d - N_a}{2} + \sqrt{\left(\frac{N_d - N_a}{2}\right)^2 + n_i^2}$$

$$= \frac{3 \times 10^{16}}{2} + \sqrt{\left(\frac{3 \times 10^{16}}{2}\right)^2 + (1.5 \times 10^{10})^2}$$

$$\underline{n_0 = 3 \times 10^{16} \text{ #/cm}^3}$$

$$(4.43) \quad n_0 p_0 = n_i^2 \rightarrow p_0 = \frac{n_i^2}{n_0}$$

$$p_0 = \frac{(1.5 \times 10^{10})^2}{3 \times 10^{16}} \Rightarrow \underline{p_0 = 7.5 \times 10^3 \text{ #/cm}^3}$$